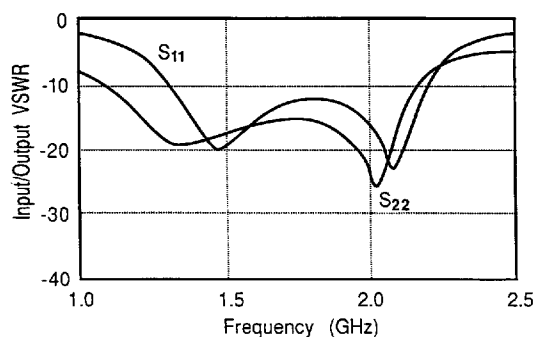
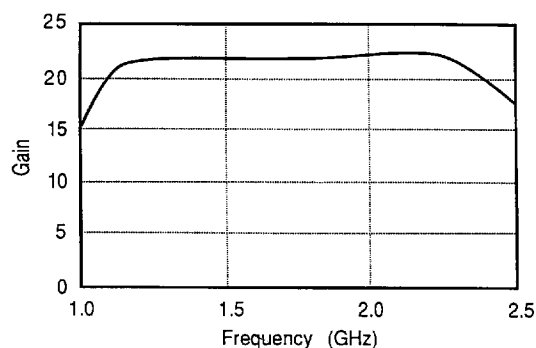


This Gallium Arsenide Monolithic Microwave Integrated circuit (GaAs) MMIC is a low noise amplifier (LNA) for use with RF frequencies in the region of 1.9GHz. Very low DC power consumption makes this part ideally suited to battery powered operation.

Features

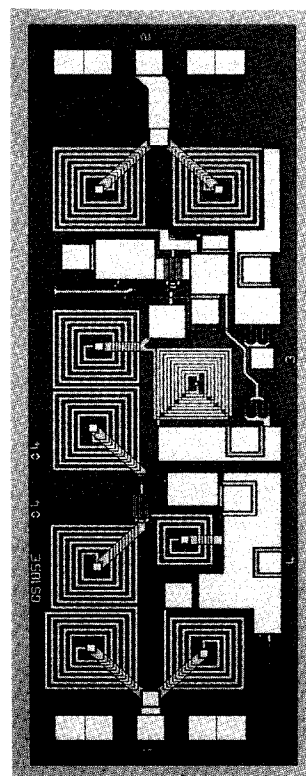
- Flat gain of 22dB vs frequency
- +3V single supply rail
- Low current consumption, 5mA
- No external matching or biasing components required

Typical Performance



GaAs MMIC LNA FOR 1.9GHz MOBILE COMMUNICATIONS

Advanced Product Information



P35-4180**Outline Specification**

Typical Performance Parameters	Vdd = 3V	Vdd = 4V	Vdd = 5V
Ids (mA)	5	5.5	6.0
FLOW (MHz)	1400	1400	1400
FHIGH (MHz)	2200	2200	2200
Gain (dB)	22	22.5	23
Gain variation with frequency (dB)	±0.3	±0.3	±0.3
Noise figure at 1.9GHz (dB)	2.3	2.4	2.5
Minimum input return loss (dB)	12	12	12
Minimum output return loss (dB)	14	15	15
Input referred 1dB compression point (dBm)	-20	-19	-18.5
Input referred third order intercept point (dBm)	-12	-9	-8
Absolute maximum input power (dBm)	3.5	5.0	5.5

Note:-

All data has been measured directly on wafer. This part will be available in an SO – 8 style plastic package from September 1994.

